

ABSTRACT OF THE DISCLOSURE

An interconnect forming method according to the present invention includes a step of forming a barrier film for metal diffusion on an insulator film, a step 5 of selectively forming a metal seed layer on the barrier film for metal diffusion using an electroless plating process, a step of selectively forming a metal conductive layer on the metal seed layer using an electroplating process, and a step of etching the 10 barrier film for metal diffusion using the metal conductive layer as a mask.